

24-V Dual-Channel Gate Driver For Large Power Switches

An addition to its EiceDRIVER portfolio, [Infineon Technologies'](#) 2ED24427N01F is 24-V dual-channel low-side gate driver with an integrated thermal pad. It can be operated with high switching frequencies as well as high peak output currents and offers an enable function. The gate driver is suitable for applications with higher switching frequencies such as power factor correction and synchronous rectification, as well as a transformer driver or a buffer driver for parallel MOSFET applications or high-current IGBT modules such as EasyPACK and EconoPACK.

The EiceDRIVER 2ED24427N01F provides a symmetrical output stage with 10-A source and sink drive capability with integrated undervoltage lockout (UVLO) protection and logic-level enable control. The gate driver is available in a DSO-8 package with a thermally efficient and exposed power pad. With 55-ns propagation delays and 450-m Ω (max) source and sink on-resistance per channel, the driver enables high switching frequencies with reduced switching losses of the power transistors.

The integrated thermal pad offers very low thermal resistance to enable reliable operation at lower temperatures under high current conditions or at higher switching frequencies. The driver is rated for operation over an industrial temperature range.

The EiceDRIVER 2ED24427N01F can be ordered now in an industry-standard DSO-8 (SOIC-8) package with a thermal pad and 2-kV HBM ESD ratings. For more information, see the 2ED24427N01F [page](#).

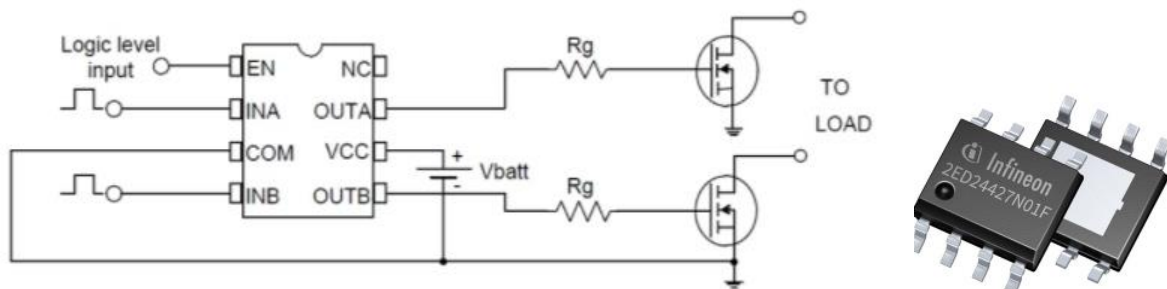


Figure. The EiceDRIVER 2ED24427N01F is a 24-V dual-channel low-side non-inverting gate driver for MOSFETs or IGBTs with typical 10-A source and sink currents in a DSO-8 package with a thermally efficient, exposed power pad. This driver IC enables higher power and faster switching frequencies in various applications, while providing a reduced PCB footprint and increased reliability by simplifying high power density system design.